

L Number	Hits	Search Text	DB	Time stamp
1	233029	resistor	USPAT; US-PGPUB	2002/10/23 11:41
2	50774	resistor and (substrate wafer)	USPAT; US-PGPUB	2002/10/23 11:41
3	22751	(resistor and (substrate wafer)) and gate	USPAT; US-PGPUB	2002/10/23 11:41
4	13939	((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)	USPAT; US-PGPUB	2002/10/23 11:41
5	12972	((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)) and (trench via open\$4 contact hole)	USPAT; US-PGPUB	2002/10/23 11:41
6	6879	((((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)) and (trench via open\$4 contact hole)) and isolat\$3	USPAT; US-PGPUB	2002/10/23 11:30
7	408	(((((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)) and (trench via open\$4 contact hole)) and isolat\$3) and (STI (shallow near5 trench near5 isolat\$3))	USPAT; US-PGPUB	2002/10/23 11:32
8	408	(((((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)) and (trench via open\$4 contact hole)) and isolat\$3) and (STI (shallow near5 trench near5 isolat\$3))	USPAT; US-PGPUB	2002/10/23 11:32
9	240964	resistor	EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:41
10	25472	resistor and (substrate wafer)	EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:41
11	2315	(resistor and (substrate wafer)) and gate	EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:41
12	1051	((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)	EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:41
13	524	((resistor and (substrate wafer)) and gate) and (dielectric insulat\$3)) and (trench via open\$4 contact hole)	EPO; JPO; DERWENT; IBM_TDB	2002/10/23 11:42